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High pressure x-ray diffraction study of the volume collapse in Ba$_{24}$Si$_{100}$ clathrate

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The high pressure stability of the silicon type-III clathrate Ba$_{24}$Si$_{100}$ has been studied by x-ray diffraction (XRD) up to a maximum pressure of 37.4 GPa. The high pressure behavior of this Si type-III clathrate appears to be analogous to the structural type-I parent Ba$_8$Si$_{46}$. An isosctructural volume collapse is observed at $\sim$23 GPa, a value higher than for Ba$_8$Si$_{46}$ (13–15 GPa). The crystallinity of the structure is preserved up to the maximum attained pressure without amorphization, which appears to be in contradiction with the interpretation given in a Raman spectroscopy study [Shimizu *et al.*, Phys. Rev. B 71, 094108 (2005)]. Nevertheless, the XRD analysis shows the appearance of a type-III disordered nanocaged-based crystalline structure after the volume collapse. Moreover, we find that the volume collapse transformation is (quasi)reversible after pressure release. Additionally, a low pressure transition first evidenced by Raman spectroscopy is also observed in our XRD study at 5 GPa; the variation of the isotropic thermal factors of Ba atoms shows a clear discontinuity at this pressure while the average positions of Ba atoms remain identical.

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I. INTRODUCTION

Inorganic clathrates based on group IV elements (C, Si, Ge, Sn) have attracted a renewed interest in the past years since their discovery in the 1960s.1,2 Indeed, due to their crystallographic structure based on nanocages (with 20, 24, or 28 atoms) more or less filled by guest atoms, their physical properties can be tuned,3,4 making such a class of materials interesting for potential technological applications in electronics, optics, or mechanics. One way to explore their properties is to use pressure as a thermodynamic variable which allows to continuously modify the interaction between the host and the guest substructures. This methodology has been followed by different scientific groups in the past decade for clathrate systems. Only very few studies on type-III clathrates under high pressure have been conducted. Grosche *et al.* have studied the superconducting behavior of type-III Ba$_{24}$Ge$_{100}$ and (Ba$_4$Na$_2$)Ge$_{100}$ germanium-based clathrates up to 3.4 GPa and in low temperature5,6 while Shimizu *et al.* have reported a Raman spectroscopy study of Ba$_{24}$Ge$_{100}$ up to 26 GPa at room temperature.8 Two published works report on the high pressure behavior of Ba$_{24}$Si$_{100}$, the compound studied in the present article; a low temperature resistivity study up to 1.15 GPa (Ref. 9) of its superconducting regime and a Raman spectroscopy study by Shimizu *et al.* at room temperature up to 27 GPa.10 To the best of our knowledge, no high pressure x-ray diffraction study of Ba$_{24}$Si$_{100}$ has been published. Let us turn to type-I silicon-based clathrates, which are structurally related, simpler, and more documented both experimentally and theoretically. In the Ba$_8$Si$_{46}$ type-I clathrate,11 it is now well established that a volume collapse takes place at pressures of 13–15 GPa.3,12,13 This unusual second-order transition is more precisely an isosctructural homothetic volume collapse (HVC), i.e., the full structure is preserved through the transition, with the relative atomic positions remaining the same during the whole process.14,15 This HVC seems to be a general trend in type-I silicon clathrates (built on Si$_{20}$ and Si$_{28}$ cages): It is observed in heavy alkaline-doped Si clathrates [K$_6$Si$_{46}$ (Refs. 16 and 17), Rb$_6$Si$_{46}$ (Ref. 18)], in alkaline-earth intercalated Si clathrates [Ba$_6$Si$_{46}$, (Ba$_6$Sr$_2$)Si$_{46}$, Ba$_8$(Si$_{40}$Ag$_6$)]$_3$,19,20 and in the halogen-doped clathrate I$_8$(Si$_{44}$I$_2$).3,21 In type-II silicon clathrates (i.e., M$_8$Si$_{136}$ with M = Na, for example) the silicon network (made of Si$_{20}$ and Si$_{28}$ cages) evolves discontinuously (first-order transition) toward the $\beta$-tin structure at 10–11 GPa (Refs. 12 and 22) (see Fig. 5 below). Is this HVC scheme also valid in the analogous Ba$_{24}$Si$_{100}$ type-III clathrate?23,24 Type-III clathrates are built from the same silicon-based Si$_{20}$ cages as in Ba$_8$Si$_{46}$ and from distorted Si$_{20}$ (in fact, the same Si$_{24}$ cages of those from Ba$_8$Si$_{46}$ with four vacancies of Si), also giving rise to cubic Si$_{10}$ cages (see Fig. 1).

The high pressure (HP) Raman spectroscopy study of Ba$_{24}$Si$_{100}$ by Shimizu *et al.*10 has evidenced two transitions. The first one, between 3.9 and 6.5 GPa, is characterized by the splitting of the 126 cm$^{-1}$ Raman mode and a general decrease of the intensity of the modes associated with the vibrations of Na atoms. The second one, at 20.7–23.2 GPa, is associated with the disappearance of all the Raman modes, which was attributed to a pressure-induced amorphization by the authors of that work. In Ba$_8$Si$_{46}$, the pressure evolution of the Raman signal shows some similitudes: At $\sim$7 GPa the lowest-frequency modes disappear, then at the HVC at $\sim$13–15 GPa, the Raman spectrum is drastically affected, showing six large bands above the HVC, and finally the Bragg
FIG. 1. (Color online) Partial crystallographic structure of Ba$_{24}$Si$_{100}$ showing the different cages around the three Ba sites and the corresponding Si sites forming the Si network [see the text for a description of Si(1), Si(2), Si(3), Si(4), Si(5), Si(6) and Ba(1), Ba(2), Ba(3) sites].

peaks of its x-ray diffraction (XRD) pattern disappear above 40 GPa, proof that Ba$_8$Si$_{46}$ becomes irreversibly amorphous at higher pressure.

In Ba$_8$Si$_{46}$ the nature of the first transition at 7 GPa is related to a change of the hybridization of Ba orbitals with Si orbitals, accompanied with a charge transfer from Ba in the small Si$_{20}$ cages toward the Si framework. The induced change of the polarizability of Ba in the large Si$_{24}$ cage shown by HP Raman scattering, the jump $\sim$5 GPa in the x-ray absorption near-edge structure (XANES) $L_3$ absorption edge of Ba (Ref. 15), and a recent analysis of HP XRD patterns by the maximum entropy method support this scenario. Another scenario related to an off-centering of Ba in large Si$_{24}$ cages could explain the first transition occurring at 5–7 GPa in Ba$_8$Si$_{46}$, but from extended x-ray-absorption fine structure (EXAFS) experiments performed at the Ba $K$ edge on Ba$_8$Si$_{46}$, we can exclude it, within the error bar of the EXAFS analysis, which is $\sim$0.3 Å (Refs. 15 and 26) in those measurements. In Ba$_{24}$Si$_{100}$, the second transition observed by HP Raman spectroscopy at $\sim$22–23 GPa was interpreted as a sign of amorphization, because of the irreversible loss of all Raman-active modes above this pressure.

In this paper we show by in situ XRD that the transition at 23 GPa does not correspond to the amorphization of the Ba$_{24}$Si$_{100}$ clathrate but to the volume collapse transition. In addition, our high pressure excursion shows that the transition is reversible, at least up to 37 GPa.

The Ba$_{24}$Si$_{100}$ sample was synthesized in a high pressure belt-type apparatus, as reported elsewhere. We started with commercial BaSi$_2$ (CERAC, 98%) and Si (Alfa, 99.9%) powders. Both precursors were mixed together and grind in the nominal ratio. The mixture was compacted in small cylindric pellets (4 mm diam and 5 mm length) and placed into a closed hexagonal boron nitride crucible. The entire assembly was introduced inside the carbon tube heater inserted in the pyrophyllite HP gasket. The temperature was previously calibrated using a chromel-alumel thermocouple. The HP-HT synthesis was performed at 1.1 GPa and 650 °C. The pressure was first increased up to 1.1 GPa, then the sample was slowly heated up to 650 °C and maintained at this temperature for 1 h, and then quenched rapidly to room temperature. Finally the pressure was released to room pressure and the sample recovered.

XRD patterns were collected using a Siemens D-500 powder diffractometer working in the Bragg-Brentano geometry at a wavelength $\lambda_{Cu,K\alpha_1} = 1.5418$ Å from 2θ = 10° to 120° in steps of 0.02°.

A Raman spectrum was also recorded at room temperature using a Jobin-Yvon HR-800 Labram spectrometer double-notch filtering and air-cooled CCD detector. The measurement was performed without heating or damaging the sample by using an adapted power of an excitation laser with a wavelength of 514 nm.

The HP in situ synchrotron XRD experiment was carried out using a He gas membrane-driven diamond-anvil cell (DAC) with diamonds having a culet size of 350 μm. Samples were loaded using nitrogen as a pressure-transmitting medium, and the pressures were determined using the ruby fluorescence method. Pressure was increased by small steps of 0.5–1 GPa and the system was left to equilibrate for 15–30 min at each pressure. Synchrotron radiation measurements were performed at the ID9A beamline of the European Synchrotron Radiation Facility via angle-dispersive diffraction techniques using monochromatic radiation $\lambda = 0.4108$ Å. Diffraction patterns were collected using image plate detection. The sample-to-detector distance and the image plate orientation angles were calibrated using a polycrystalline powder Si standard. The two-dimensional diffraction images were analyzed using the FIT2D software, yielding one-dimensional intensity versus diffraction angle 2θ patterns.

III. RESULTS AND DISCUSSION

A. Ambient pressure characterization of the Ba$_{24}$Si$_{100}$ sample

Figure 2 shows the XRD pattern and the Raman spectrum (inset of Fig. 2) of our polycrystalline Ba$_{24}$Si$_{100}$ sample obtained at ambient conditions. Both are in good agreement with the ones published in previous works. The XRD pattern shows that the sample is nearly single phase and contains traces of remaining Si and cubic BaSi$_2$ phases (their main Bragg peaks indicated an overlap with the reflections of Ba$_{24}$Si$_{100}$). The cubic lattice parameter refined from this XRD pattern at ambient pressure [$\alpha \approx 14.061(1)$ Å] is in agreement with those already reported.
B. Description of the method based on Rietveld refinements used for the XRD patterns analysis

The structural parameters of Ba$_{24}$Si$_{100}$ were refined from XRD patterns by the Rietveld method using the software FULLPROF.$^{28}$ Data points within the range $1.90^\circ < 2\theta < 24^\circ$ were taken into account. The profile shape was calculated based on a pseudo-Voigt function. The background was fitted using a linear interpolation between points.

The Ba$_{24}$Si$_{100}$ clathrate crystallographic structure was refined assuming a cubic lattice (space group $P_{4}132$, No. 213) of type-III clathrate published previously (Fig. 1), i.e., Si(1) at 8$c$($x$, $x$, $x$) with $x = 0.0362$, Si(2) at 24$e$ (0.2038, 0.0427, 0.0001), Si(3) at 12$d$ ($1/8$, $y$, $y$ + 1/4) with $y = 0.1696$, Si(4) at 24$e$ (0.2387, 0.9394, 0.8752), Si(5) at 24$e$ (0.4156, 0.8605, 0.0769), Si(6) at 8$c$($x$, $x$, $x$) with $x = 0.3256$, Ba(1) at 8$c$($x$, $x$, $x$) with $x = 0.1887$ in the small Si$_{20}$ cages, Ba(2) at 4$b$ ($7/8$, $7/8$, $7/8$) in cubic Si$_{8}$ cages, and Ba(3) at 12$d$ ($1/8$, $y$, $y$ + 1/4) with $y = 0.8072$ in the distorted Si$_{20}$(vacancy)$_{4}$ cages. During the refinement of the XRD patterns the 14 structural parameters of the nine Wyckoff sites (three barium and six silicon sites) of Ba$_{24}$Si$_{100}$ were refined. All the Debye-Waller factors of the atoms were chosen as being isotropic.

In Fig. 3 we present the observed, calculated, and difference curves of the Ba$_{24}$Si$_{100}$ XRD pattern at ambient pressure (in the DAC) after Rietveld refinement; there is good agreement between the experimental and the calculated profiles. Figure 4 shows some XRD patterns during compression of the sample up to 37.4 GPa (upper part) and during pressure release (lower part). All the Bragg peaks shift to larger angles, showing the shrinkage of the cubic Ba$_{24}$Si$_{100}$ lattice.

C. Pressure-induced evolution in Ba$_{24}$Si$_{100}$

1. Phase transitions and bulk modulus

Figure 4 shows some XRD patterns during compression of the sample up to 37.4 GPa (upper part) and during pressure release (lower part). All the Bragg peaks shift to larger angles, showing the shrinkage of the cubic Ba$_{24}$Si$_{100}$ lattice. In particular, the XRD pattern of our sample is still present above 23 GPa, and despite the broadening of the peaks during the pressurization from ambient conditions to 37.4 GPa and decompression down to the full release of pressure (from top to bottom).
FIG. 5. (Color online) Variation of the relative volume of Ba$_{24}$Si$_{100}$ type-III clathrate vs pressure compared with other silicon type-I $M_8$Si$_{46}$ ($M = \text{Na, K, Rb, Ba, I}$) and type-II Si$_{136}$ clathrates.

The pattern remains qualitatively the same than the one at ambient pressure. Remarkably enough, we keep observing XRD crystalline-type patterns above 23 GPa, i.e., beyond the pressure where Shimizu et al. observed the complete attenuation of all the Raman peaks of Ba$_{24}$Si$_{100}$.\textsuperscript{10}

As illustrated in Figs. 5 and 6(a) (variation of the relative volume of the lattice), the Ba$_{24}$Si$_{100}$ lattice parameter decreases continuously with pressure, reaching 13.04(1) Å at 23 GPa. At this pressure the relative volume of the lattice is 80% of the initial one (i.e., a reduction of 20% of the cubic lattice). Above this point, the reduction of the relative volume changes its regime, as shown by the kink in the $V/V_0$ curve as a function of pressure $\sim$23 GPa (Fig. 5). This behavior of the relative volume is very similar to the one in type-I silicon clathrates $M_8$Si$_{46}$ ($M = \text{Ba, Sr, Rb, K, Na, I}$), the kink in the relative volume curve being the signature of the volume collapse of the lattice. At this point, we notice that Ba$_{24}$Si$_{100}$ has a higher volume collapse pressure than the ones in Na$_8$Si$_{46}$, or Ba$_8$Si$_{46}$ (13–15 GPa) and in the nonintercalated Si$_{136}$ clathrate (10–11 GPa). The volume collapse pressure of our type-III clathrate exhibits a value much closer to the case of K$_8$Si$_{46}$ (20–26 GPa) or Rb$_{6.15}$Si$_{46}$ (23–25 GPa) (see Fig. 5 and Table I). However, this value remains lower than the pressure for which the collapse is observed in I$_8$(Si$_{14}$I$_2$) or Ba$_8$(Ag$_{46}$Si$_{40}$) ($\sim$35 and 28 GPa, respectively), i.e., a compound with initial lattice parameters higher than the ones of the Ag unsubstituted compound. Increasing the size of the silicon cages and conserving the same guest atoms in the cages appears then to push the lattice collapse to higher pressures.

This relationship between the size of the host network and the pressure instabilities was also recently evidenced in Ge-based clathrates by Kume et al.$^{29}$ In addition, in Ba$_8$(Ga$_{16}$Ge$_{30}$), these authors have demonstrated that before the volume collapse the displacement of host atoms in the Wyckoff $24k$ position during the compression of the clathrate gives rise to the deformation of the hexagonal ring in the large (Ga,Ge)$_{24}$ cage. In Ba$_{24}$Si$_{100}$, the absence of four Si atoms forming these hexagonal rings in the normal Si$_{24}$ cages (replaced by Si$_{24}$ cages with four vacancies) then could be at the origin of its higher volume collapse pressure. We will discuss the internal structure changes in more detail later in the article.

TABLE I. Pressures of volume collapse and amorphization for type-III Ba$_{24}$Si$_{100}$ as compared to other type-I $M_8$Si$_{46}$ and type-II $M_x$Si$_{136}$ clathrates. See also Fig. 5.

<table>
<thead>
<tr>
<th>Compound</th>
<th>$P_{\text{collapse}}$ (GPa)</th>
<th>$P_{\text{amorphization}}$ (GPa)</th>
<th>Ref.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ba$<em>{24}$Si$</em>{100}$</td>
<td>23.0(5)</td>
<td>$&gt;37$ GPa</td>
<td>This work</td>
</tr>
<tr>
<td>Ba$<em>8$Si$</em>{46}$</td>
<td>14(1)</td>
<td>40(3)</td>
<td>14</td>
</tr>
<tr>
<td>Ba$<em>8$(Ag$</em>{46}$Si$_{40}$)</td>
<td>28(3)</td>
<td>$&gt;40$ GPa</td>
<td>Our work$^4$</td>
</tr>
<tr>
<td>Rb$<em>{6.15}$Si$</em>{46}$</td>
<td>24(1)</td>
<td>33(1)</td>
<td>18</td>
</tr>
<tr>
<td>K$<em>8$Si$</em>{46}$</td>
<td>23(3)</td>
<td>32(3)</td>
<td>16</td>
</tr>
<tr>
<td>Na$<em>8$Si$</em>{46}$</td>
<td>13(2)</td>
<td>–</td>
<td>14</td>
</tr>
<tr>
<td>I$<em>8$(Si$</em>{14}$I$_2$)</td>
<td>35(3)</td>
<td>47(3)</td>
<td>14</td>
</tr>
<tr>
<td>Na$<em>1$Si$</em>{136}$</td>
<td>11(1)</td>
<td>–</td>
<td>12.22</td>
</tr>
</tbody>
</table>

$^4$Unpublished.
In Fig. 6 (a), our $V/V_0$ $\text{Ba}_2\text{Si}_{100}$ data points upon compression in the low pressure range 0–22.5 GPa were fitted using a Murnaghan equation-of-state model to obtain the bulk modulus $K_0$ and its pressure derivative $K'_0$. The values obtained by this procedure are $K_0 = 64.9(3)$ GPa and $K'_0 = 3.75(4)$; this value of $K'_0$ is very close to the ones usually found for other type-I and type-II Si clathrates by San-Miguel et al. 12 (3.6, a value obtained by a Murnaghan fitting analysis of theoretical calculated data points for $\text{Si}_{136}$) and for Si-diamond $[3.8(4)$ (Ref. 30)].

We have also used an alternative fitting procedure based on the normalized or reduced stress-strain variables $F$ and $f$. 31,32 The Eulerian strain parameter $f$ and the normalized pressure $F$ are defined as follows: $f = 1/2[(V/V_0)^{-2/3} - 1]$ and $F = -3f(1 + 2f)^{2/3} - 1$. This formalism yields the second-order finite strain equation $F = K_0[1 - 1.5(4 - K'_0)f]$. As shown in Fig. 7, in the different pressure regions, in particular, below 23 GPa i.e., before the volume collapse, the $F$–$f$ plot is in fact a straight line, and from its intercept as $f$ goes to zero and its slope, we obtain $K_0 = 65.0(3)$ GPa and $K'_0 = 3.90(6)$. This is in agreement with the values obtained with our previous approach. To summarize, $\text{Ba}_2\text{Si}_{100}$ shows a bulk modulus of $K_0 = 65.0(4)$ GPa with $K'_0 = 3.8(1)$, in that sense it is more compressible than other inorganic Si-based clathrates. This is particularly visible in Fig. 5 (see also Table II, which summarizes also the data available in the literature for different types of silicon clathrates), where one can see that the relative volume of the type-III silicon $\text{Ba}_2\text{Si}_{100}$ clathrate decreases faster with pressure (before the HVC) than the other type-I $M_8\text{Si}_{46}$ or type-II $M_7\text{Si}_{136}$. It seems that a general trend in clathrates formed of Si$_{20}$ and Si$_{24}$ cages (types I and III) is that when all the silicon cages are filled at their maximal content, the bulk modulus of the corresponding clathrates are in the range of 85–95 GPa; if one type of cage is quasempt (the case of Rb$_6\text{Si}_{46}$) this bulk modulus drops to a lower value (78 GPa); and finally when a part of the atoms forming the cages are absent (as in our present $\text{Ba}_2\text{Si}_{100}$ compound), the silicon network is less strong to sustain the external pressure and more compressible, and as a consequence the bulk modulus decreases again to 65 GPa.

2. Evolution of the internal structural parameters

The XRD patterns were fitted by Rietveld refinement up to 25 GPa. As mentioned before, the atomic positions were refined, keeping the isotropic thermal factors (Biso) constant (at their initial values refined at room pressure) and refining the profile parameters of the peaks. In a second refinement protocol, the Biso were simultaneously fitted with the internal structural parameters (peak profile and lattice parameters). Both approaches give the same result, represented in Fig. 8: The relative positions of the atoms inside the lattice do not change up to the volume collapse at 23 GPa. We note that the transition seen by Raman spectroscopy 10 between 3.9 and 6.5 GPa is not detected here. Between 23 and 25 GPa, i.e., at the beginning of the volume collapse, it

![FIG. 7. (Color online) Normalized pressure ($F$) as a function of the Eulerian strain ($f$) induced in the lattice of $\text{Ba}_2\text{Si}_{100}$ under pressure.](image)

![FIG. 8. (Color online) Relative position of the atoms in the $\text{Ba}_2\text{Si}_{100}$ lattice as a function of pressure, obtained from Rietveld refinement. Error bars are smaller than the size of the symbols.](image)
seems that some Si atoms start to move slightly from their relative position Si(3) [common in Si\textsubscript{20} and Si\textsubscript{20(vacancy)}\textsubscript{4} cages] and Si(5) [common in the three types of cages; for example, see Fig. 1], while the average positions of the three Ba sites is not affected. This is the sign that some disorder starts to appear in the silicon-host network. As a consequence, the average Si-Si distances are changed, and some of them are strongly renormalized. This is the case of the ones around the central Si\textsubscript{3} atom, common in three kinds of cages, for example, the Si(1)-Si(5) distance [i.e., the one common in pseudocubic Si\textsubscript{8} and Si\textsubscript{20(vacancy)}\textsubscript{4} cages] which increases from 3.85(4) Å at 22.3 GPa to 4.28(5) Å at 24.8 GPa (i.e., a change of 11%). We remark that before the collapse all the Si nanocages are deformed isostructurally, with all the distances decreasing at the same rate. This case is different from the case of the Ge/Ga-based clathrate Ba\textsubscript{24}(Ga\textsubscript{16}Ge\textsubscript{30}) studied by Kume et al.,\textsuperscript{29,34} where the relative position of the Ge/Ga 2k site changes with pressure (while the other sites stay at the same relative position) before the lattice collapse; this movement of the 2k site is certainly related to the volume collapse in this Ga/Ge type-I clathrate. At this point we cannot make a direct relationship between the lowest-energy Raman mode and the average guest-host distance, which was proposed by the previous cited work of Kume et al.\textsuperscript{29} to evidence the collapse critical point, characterized by the softening of the low-energy phonon. Nevertheless, the work of Shimizu et al.\textsuperscript{10} show that the 48 cm\textsuperscript{-1} mode of Ba\textsubscript{24}Si\textsubscript{100}, related to the Ba(3) large Si\textsubscript{20(vacancy)}\textsubscript{4} cage, hardens at the beginning of the compression, then flattens at \(\sim 20\) GPa, and seems to soften just below the onset of the volume collapse. Another key parameter related to the lattice collapse can be the mode of the Ba(2) encaged in the pseudocubic Si\textsubscript{8}. These issues are certainly interesting to investigate in more detail to determine if a critical behavior of one of the low-energy phonons of Ba\textsubscript{24}Si\textsubscript{100} are at the origin of its volume collapse.

Above 25 GPa, the refinement is unstable and diverges, probably because it becomes impossible to modelize the structure using the initial structural model, the disorder of the structure being too strong.

Figure 9 shows the variation of the refined values of isotropic thermal factors obtained from the Rietveld refinement. The one from the silicon atoms (taken to be identical for all Si atoms) does not show a large variation up to the volume collapse at 23 GPa. In contrast, the variation in the three thermal factors of Ba atoms shows three distinguishable regimes: Below 5 GPa, they decrease moderately, then they increase discontinuously to the second regime, where Biso of Ba\textsubscript{2} (in cubic Si\textsubscript{8} cages) and Ba\textsubscript{3} (in Si\textsubscript{24} cages with four vacancies) decrease again slowly with pressure while the one of Ba\textsubscript{1} (in regular Si\textsubscript{3} cages) stays constant up to 23 GPa. This change in the thermal factors of Ba atoms at 5 GPa is not an artifact due to the nitrogen freezing because nitrogen solidifies at \(\sim 2.4\) GPa (at room temperature).\textsuperscript{35} Moreover, this result is consistent with the general decrease of the intensity of the modes associated with the vibrations of Ba atoms measured by Raman spectroscopy between 3.9 and 6.5 GPa.\textsuperscript{10} This is also a proof that the nature of the transmitting medium (argon in the Raman spectroscopy study and nitrogen here) does not influence the transition observed here.

Finally, between 23 and 25 GPa, i.e., in the first stage of the volume collapse, all the three Ba Biso increase hugely, in particular, the one of Ba\textsubscript{2} (atom in large cubic Si\textsubscript{8} cage) reaching very large values; this site of Ba\textsubscript{2} is the most affected by the volume collapse and the large values attained (unphysical) of Biso are a sign of a strongly disordered site.

The two transitions are also marked in the variation of the shape parameter of the Ba\textsubscript{24}Si\textsubscript{100} Bragg peaks (ratio between the Gaussian and Lorentzian contributions) with pressure.

3. Above the volume collapse at 23 GPa

As described before, at 23 GPa the Ba\textsubscript{24}Si\textsubscript{100} lattice collapses, as shown by the kink in the curve of its relative volume, a sign of the sudden change in compressibility of the material [Figs. 5 and 6(a)]. The change in compressibility before and after 23 GPa is also clearly visible on the

FIG. 9. (Color online) Isotropic thermal factors of Ba(1, 2, and 3) atoms (top panel) and Si atoms (all sites constrained to the same value) (bottom panel) of Ba\textsubscript{24}Si\textsubscript{100} as a function of pressure, obtained from Rietveld refinement. Inset of top panel: Variation of the shape parameter of the Ba\textsubscript{24}Si\textsubscript{100} Bragg peaks (ratio between the Gaussian and Lorentzian contributions) with pressure.
F–f plot (Fig. 7), which shows a discontinuity at $f = 0.08$, corresponding to $F = 23$ GPa.

No halo is found on the XRD images above the volume collapse at 23 GPa, which is a usual sign of amorphization, as observed for instance above 33 GPa in Rb$_{6.15}$Si$_{46.18}$.

Moreover, at the highest pressure reached, 37.4 GPa, we still have diffraction peaks with no significant change of the relative intensities. The amorphization pressure in this type-III clathrate is then at least higher than the ones of Rb$_{6.15}$Si$_{46}$ and K$_3$Si$_{46}$, $\sim$32–33 GPa (see Table I) and finally of the same order than other Si-based type-I clathrates.

However, at very high pressure, we observe a broadening, as shown in Fig. 6(b) for the (221) Bragg peak ($\sim$5° at ambient pressure), all the diffraction peaks become quickly broader above 23 GPa; this is the case also for the most intense (431) and (520) reflections.

As mentioned in the previous section, it was not possible to refine the atomic positions at such high pressure, but the important point is that we do observe a diffraction signal at 37.4 GPa while the typical Raman spectrum of Ba$_{24}$Si$_{100}$ is fully lost at 23.2 GPa. This situation has also been observed in Sr$_6$(Ga$_{16}$Ge$_{30}$), Ba$_4$(Ga$_{16}$Ge$_{30}$),$^{29,34}$ and K$_8$(Sb$_8$Ge$_{38}$),$^{35}$ where XRD peaks are still present even when the characteristic Raman spectra of the clathrate structure are lost. All these observations suggest that, in Ba$_{24}$Si$_{100}$, above 23 GPa, the average clathrate structure even if preserved, it is probably highly distorted. This may lead to a change of selection rules and result in spread and weak Raman signal similar to the one of an amorphous structure.

Concerning this point, the case of the germanium-based Ba$_{24}$Ge$_{100}$ clathrate could be analogous to the one of Ba$_{24}$Si$_{100}$. In fact, Shimizu et al.$^5$ found in a Raman study the amorphization of Ba$_{24}$Ge$_{100}$ at pressures above 22 GPa based on similar arguments for Ba$_{24}$Si$_{100}$. It should be then worth considering that the observed transition at 22 GPa could correspond to a volume collapse associated to a distorted-cage clathrate phase, as for Ba$_{24}$Si$_{100}$. Further studies (XRD under HP, for example) are needed.

A second point is illustrated in Fig. 10, where it is compared the XRD pattern of our Ba$_{24}$Si$_{100}$ powder in the DAC before compression and after an excursion at 37.2 GPa, at nearly zero pressure (after pressure release). The XRD patterns are identical (the peaks are slightly broader because of defaults created during the compression) proving that the transition at 23 GPa is quasi reversible. The comparison shows also that the Bragg peaks are at a slightly lower angle after compression, i.e., the clathrate lattice has expanded a little bit after this high pressure excursion. It is probably due to the fact that the cage distortions induced above 22 GPa are not completely released even after pressure release.

Our interpretation of all these results is that the silicon network remains ordered in the initial structure up to the volume collapse. Then, at the volume collapse, a strong disorder appears in all the Si sites leading to the annihilation of the Raman-active modes. The nanocage architecture is nevertheless maintained and no amorphization is reached. In fact, even at 37.4 GPa (broad) Bragg peaks still exist, and after full decompression,(nearly) the same initial XRD pattern can be recovered. This last fact points to the formation of a nanocage-based disordered structure after the volume collapse which, on pressure release, reverses toward the initial ordered structure (at least up to 37.4 GPa). The volume collapse occurring at 23 GPa is then reversible.

Finally, let us consider the first transition at 5 GPa, evidenced by Raman spectroscopy$^{10}$ and in our study. Our data shows that it is related to the Ba atoms which show a step to a larger amplitude of their oscillation above 5 GPa. This could be the sign of an off-centering (dynamic or static) of the Ba positions relatively to the center of the Si cages. From our data, we cannot conclude if some Ba sites are split in different static sites with a hopping between them or not, because all their average positions stay the same across the transition at 5 GPa. Nevertheless, if this splitting exists, it should remain small and probably undetectable by powder diffraction.

IV. CONCLUSION

The silicon type-III clathrate Ba$_{24}$Si$_{100}$ has been studied by powder x-ray diffraction at high pressure using a diamond anvil cell and nitrogen as a pressure-transmitting medium. It is found that Ba$_{24}$Si$_{100}$ has a smaller bulk modulus [with $K_0 = 65.0(4)$ GPa] than the other Si-based clathrates, with similar $K_0$ [3.8(1)].

In agreement with the previous high pressure study of Shimizu et al. using Raman spectroscopy,$^{10}$ two transitions are found, at 5 and 23 GPa, but our interpretation for the second one differs from the one proposed by Shimizu et al. Similar to type-I silicon clathrates $M_8$Si$_{46}$, Ba$_{24}$Si$_{100}$ undergoes a volume collapse which is observed at $\sim$23 GPa, a value higher than for Ba$_8$Si$_{46}$ (13–15 GPa) which is built from the same Si$_{24}$ cages but with full Si$_{24}$ cages, whereas Ba$_{24}$Si$_{100}$ has four silicon vacancies on its Si$_{24}$ cages. The presence of these vacancies and of a third barium site in a cubic Si$_8$ cage might be the
origin of its lower bulk modulus but higher stability before the volume collapse.

In the lower pressure phase transition, the Si network is not affected, but the Ba atoms show a pronounced discontinuous positive variation of their isotropic thermal factors, which we interpret as a sign of random disordering of the encaged atoms with an associated change of their hybridization with the Si network. Then, at the second transition at 23 GPa, the host network and guest atoms are more strongly affected, probably with the creation of a very distorted and disordered structure. This disordered but nanocage-based structure explains why Shimizu et al. observed the full disappearance of the Raman modes of Ba$_{24}$Si$_{100}$. This form of disorder for pressures above 23 GPa cannot be considered as an amorphization, as proved by the observation of the typical XRD pattern of Ba$_{24}$Si$_{100}$ (with very broad Bragg peaks) up to 37.4 GPa. Moreover, the collapse of the lattice at 23 GPa is reversible at least up to 37.4 GPa.